

Standard Recovery Diodes (Stud Version), 12 A



DO-203AA (DO-4)

FEATURES

- High surge current capability
- Stud cathode and stud anode version
- Wide current range
- Types up to 1200 V V_{RRM}
- RoHS compliant
- Designed and qualified for industrial and consumer level



TYPICAL APPLICATIONS

- Battery charges
- Converters
- Power supplies
- Machine tool controls

PRODUCT SUMMARY

$I_{F(AV)}$	12 A
-------------	------

MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{F(AV)}$		12	A
	T_C	144	°C
$I_{F(RMS)}$		19	A
I_{FSM}	50 Hz	265	A
	60 Hz	280	
I^2t	50 Hz	351	A ² s
	60 Hz	320	
V_{RRM}	Range	100 to 1200	V
T_J		- 65 to 175	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	VOLTAGE CODE	V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	$V_{R(BR)}$, MINIMUM AVALANCHE VOLTAGE V ⁽¹⁾	I_{RRM} MAXIMUM AT $T_J = 175$ °C mA
12F(R)	10	100	150	-	12
	20	200	275	-	
	40	400	500	500	
	60	600	725	750	
	80	800	950	950	
	100	1000	1200	1150	
	120	1200	1400	1350	

Note

(1) Avalanche version only available from V_{RRM} 400 V to 1200 V

FORWARD CONDUCTION							
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS	
Maximum average forward current at case temperature	I _{F(AV)}	180° conduction, half sine wave			12	A	
					144	°C	
Maximum RMS forward current	I _{F(RMS)}				19	A	
Maximum on-repetitive peak reverse power	P _R ⁽¹⁾	10 μs square pulse, T _J = T _J maximum			7	K/W	
Maximum peak, one-cycle forward, non-repetitive surge current	I _{FSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	265	A	
		t = 8.3 ms			280		
		t = 10 ms	100 % V _{RRM} reapplied		225		A ² s
		t = 8.3 ms			235		
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		351		
		t = 8.3 ms			320		
		t = 10 ms	100 % V _{RRM} reapplied		250		
		t = 8.3 ms			226		
Maximum I ² √t for fusing	I ² √t	t = 0.1 to 10 ms, no voltage reapplied			3510	A ² √s	
Low level value of threshold voltage	V _{F(TO)1}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum			0.77	V	
High level value of threshold voltage	V _{F(TO)2}	(I > π x I _{F(AV)}), T _J = T _J maximum			0.97		
Low level value of forward slope resistance	r _{f1}	(16.7 % x π x I _{F(AV)} < I < π x I _{F(AV)}), T _J = T _J maximum			10.70	mΩ	
High level value of forward slope resistance	r _{f2}	(I > π x I _{F(AV)}), T _J = T _J maximum			6.20		
Maximum forward voltage drop	V _{FM}	I _{pk} = 38 A, T _J = 25 °C, t _p = 400 μs rectangular wave			1.26	V	

Note

(1) Available only for avalanche version, all other parameters the same as 12F

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating temperature range	T _J		- 65 to 175	°C
Maximum storage temperature range	T _{Stg}		- 65 to 200	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	2	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.5	
Allowable mounting torque		Not lubricated threads	1.5 + 0 - 10 %	N · m
			13	lbf · in
		Lubricated threads	1.2 + 0 - 10 %	N · m
			10	lbf · in
Approximate weight			7	g
			0.25	oz.
Case style		See dimensions - link at the end of datasheet	DO-203AA (DO-4)	



ΔR_{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.33	0.26	$T_J = T_{J \text{ maximum}}$	K/W
120°	0.41	0.44		
90°	0.53	0.58		
60°	0.78	0.81		
30°	1.28	1.29		

Note

- The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

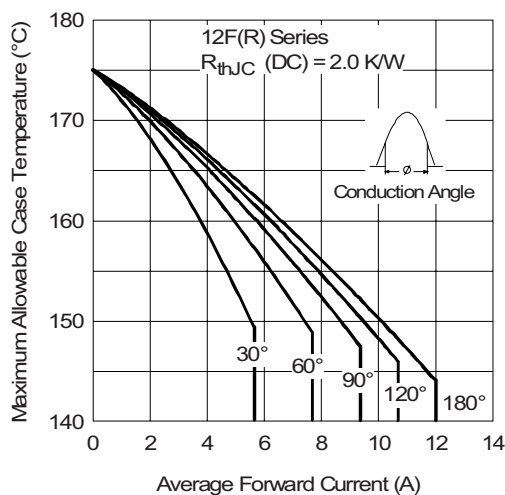


Fig. 1 - Current Ratings Characteristics

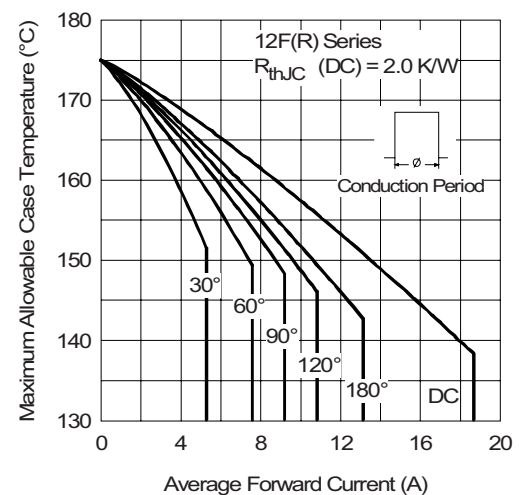


Fig. 2 - Current Ratings Characteristics

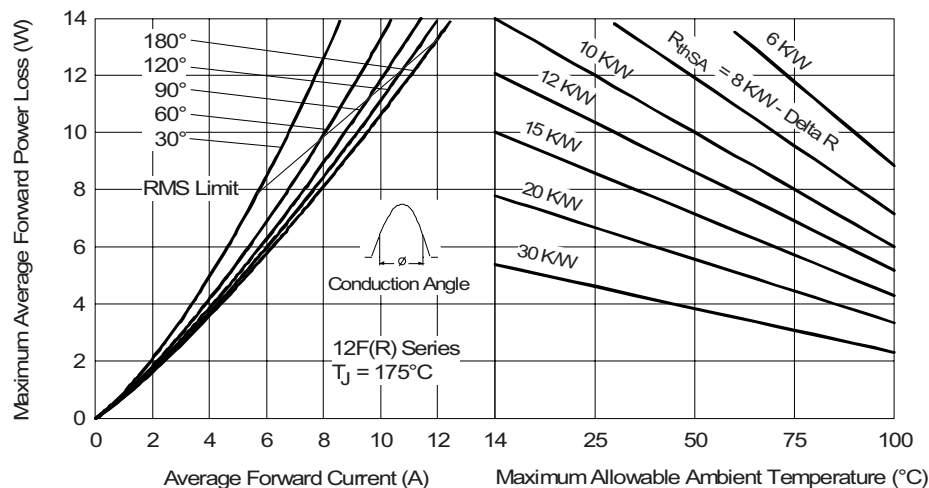


Fig. 3 - Forward Power Loss Characteristics

12F(R) Series

Vishay High Power Products Standard Recovery Diodes
(Stud Version), 12 A

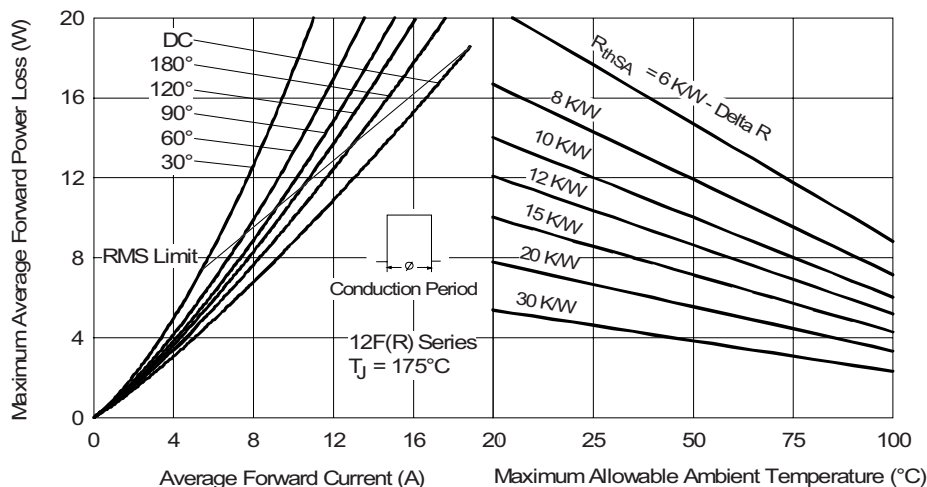


Fig. 4 - Forward Power Loss Characteristics

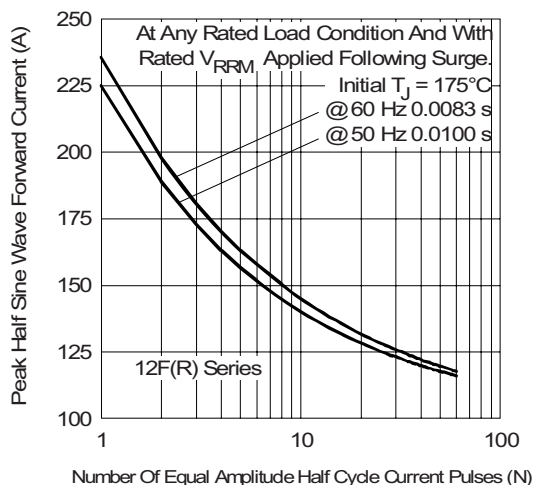


Fig. 5 - Maximum Non-Repetitive Surge Current

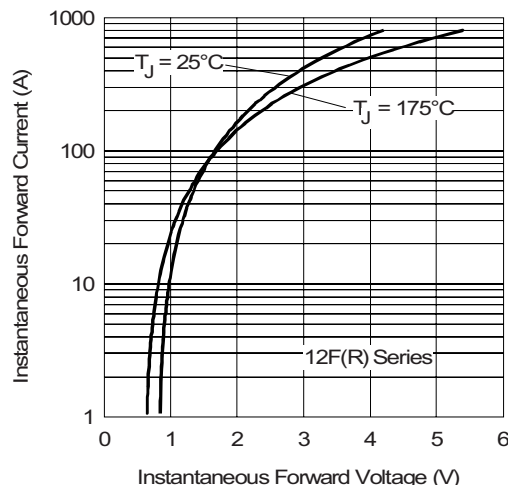


Fig. 7 - Forward Voltage Drop Characteristics

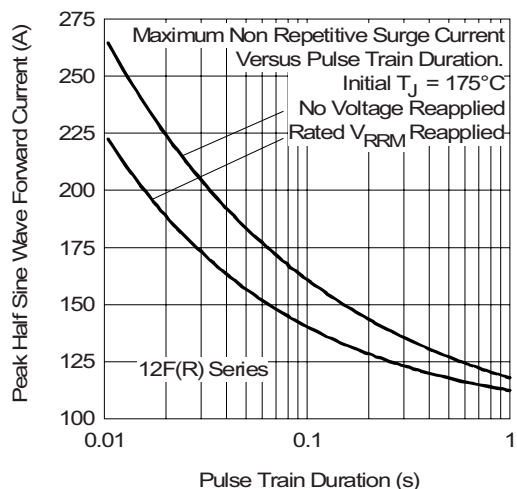


Fig. 6 - Maximum Non-Repetitive Surge Current

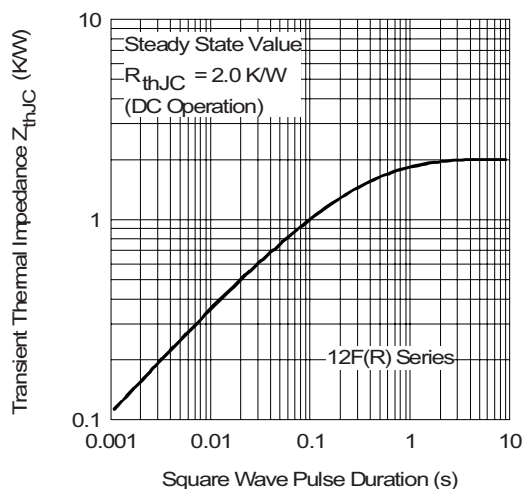


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



ORDERING INFORMATION TABLE

Device code	12	F	R	120	M
	1	2	3	4	5
	1 - Current rating: Code = $I_{F(AV)}$ 2 - F = Standard device 3 - None = Stud normal polarity (cathode to stud) R = Stud reverse polarity (anode to stud) 4 - Voltage code x 10 = V_{RRM} (see Voltage Ratings table) 5 - None = Stud base DO-203AA (DO-4) 10-32UNF-2A M = Stud base DO-203AA (DO-4) M5 x 0.8 (not available for avalanche diodes)				

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95311



Disclaimer

All product specifications and data are subject to change without notice.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained herein or in any other disclosure relating to any product.

Vishay disclaims any and all liability arising out of the use or application of any product described herein or of any information provided herein to the maximum extent permitted by law. The product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein, which apply to these products.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications unless otherwise expressly indicated. Customers using or selling Vishay products not expressly indicated for use in such applications do so entirely at their own risk and agree to fully indemnify Vishay for any damages arising or resulting from such use or sale. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

Product names and markings noted herein may be trademarks of their respective owners.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.